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(54) Ta SPUTTERING TARGET AND ITS PRODUCTION

(11) 6-264232 (A) (43) 20.9.1994 (19) JP
(21) Appl. No. 5-79055 (22) 12.3.1993
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(51) Int. Cl.⁸. C23C14/34, C22C27/02, C22F1/18

PURPOSE: To form a thin film excellent in uniformity by using a target formed from a plastically worked material of Ta having a specified content of gaseous components and a specified average grain diameter.

CONSTITUTION: This Ta sputtering target is formed from a plastically worked material of refined Ta having ≤ 100 ppm total content of gaseous components and ≤ 1 mm average grain diameter. A Ta ingot having ≤ 100 ppm total content of gaseous components is cold-worked at $\geq 90\%$ rate of working and recrystallized by heat treatment at 900-1,300°C heating temp. in ≤ 0.1 mmbar vacuum. The target can be expected to contribute largely toward improving the performance of a member utilizing a thin Ta or Ta alloy film.